Single Phase Diode Bridge
KBPC1

Key Parameters

I_O	=	3	A
V_{RRM}	=	50 - 1000	V
I_{FSM}	=	50	A
I^2t	=	12.5	A^2s

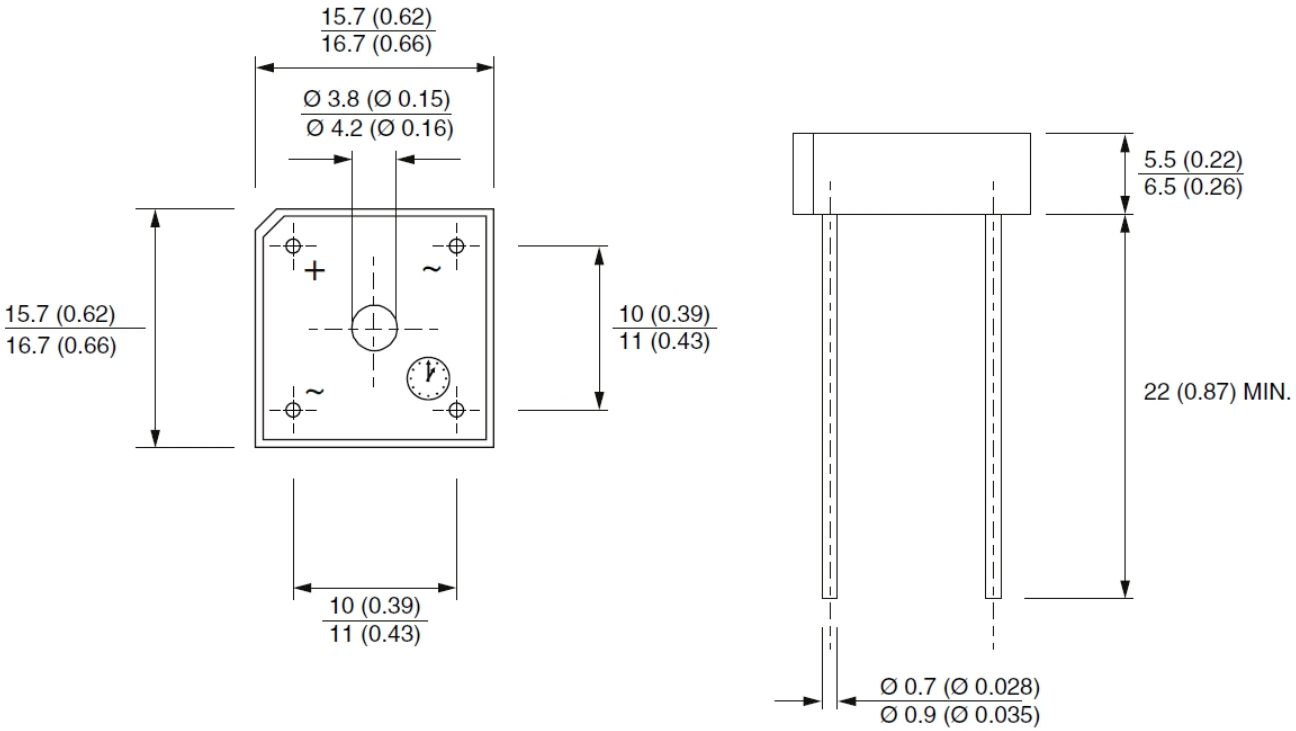
Properties

- Compact construction
- High surge current capability
- Low reverse leakage current
- Low power loss, high efficiency

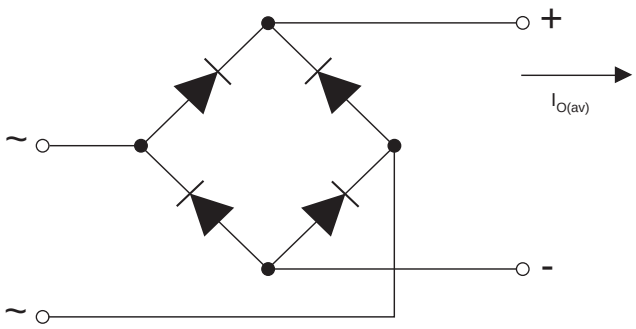
MAXIMUM ALLOWABLE RATINGS AND ELECTRICAL CHARACTERISTICS

Symbols, parameters and values									Unit
V_{RRM}	Repetitive peak reverse voltage	50	100	200	400	600	800	1000	V
I_O	Average rectified output current	Resistive load, T_C = 50 °C Capacitive load, T_C = 50 °C						3 2.4	A A
I_{FSM}	Non repetitive peak forward surge current	50 Hz 60 Hz						50 55	A A
V_{FM}	Forward voltage per leg	I_{FM} = 1.5 A						1.1	V
I_{RM}	Typical peak reverse leakage per diode	T_C = 25 °C T_C = 150 °C						10 1.0	µA mA
I^2t	I^2t rating for fusing	50 Hz 60 Hz						12.5 11.4	A^2s A^2s
W	Weight							5	g
T_j, T_{STG}	Operation and storage temperature range							-40...+150	°C

DIMENSIONS



TOPOLOGY OF INTERNAL CONNECTION



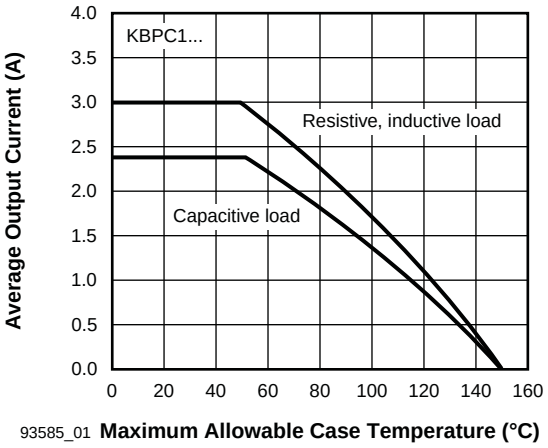


Fig. 1 - Case Temperature Ratings

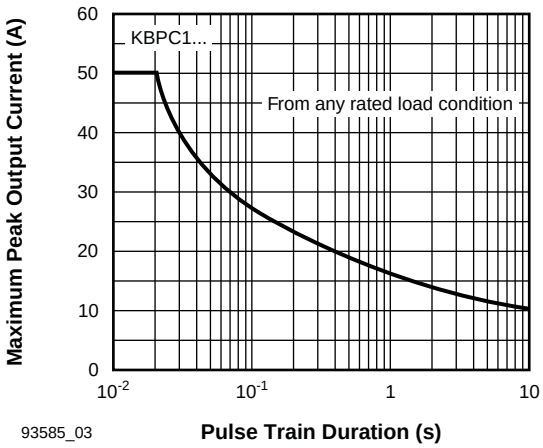


Fig. 2- Non-Repetitive Surge Ratings